



Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	4	kV

**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value	Unit	
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	35	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
$I_H$	$I_T=500mA$		MAX.	40	mA
dV/dt	$V_D=670V$ Gate Open $T_j=125$		MIN.	800	V s
(dl/dt)c	$j=125$		MIN.	10	A/ms
$t_{on}$	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	7	s
$t_{off}$				50	

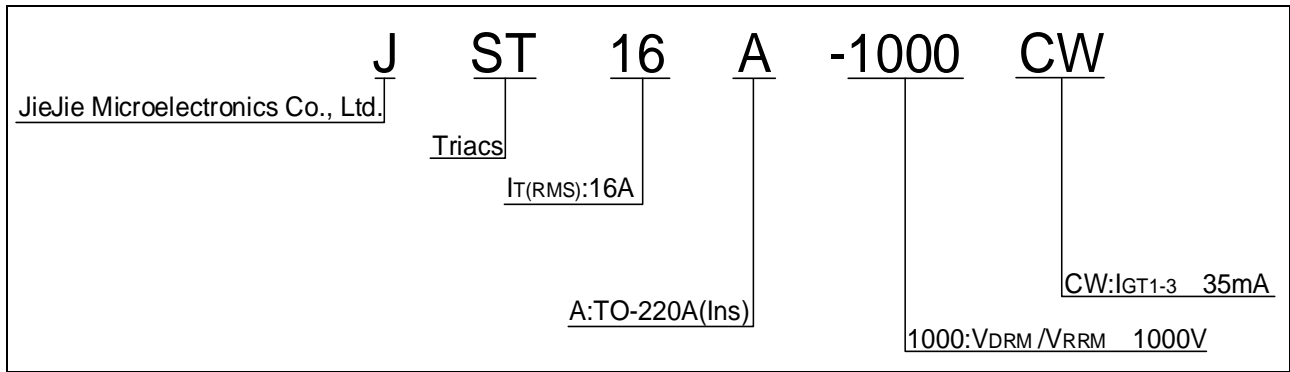
**STATIC CHARACTERISTICS**

Symbol	Parameter	Value(MAX.)	Unit	
$V_{TM}$	$I_{TM}=22.5A t_p=380 s$ $T_j=25$	1.5	V	
$V_{TO}$	Threshold voltage $T_j=125$	0.77	V	
$R_D$	Dynamic resistance $T_j=125$	32		
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	10	A
$I_{RRM}$		$T_j=125$	1	mA

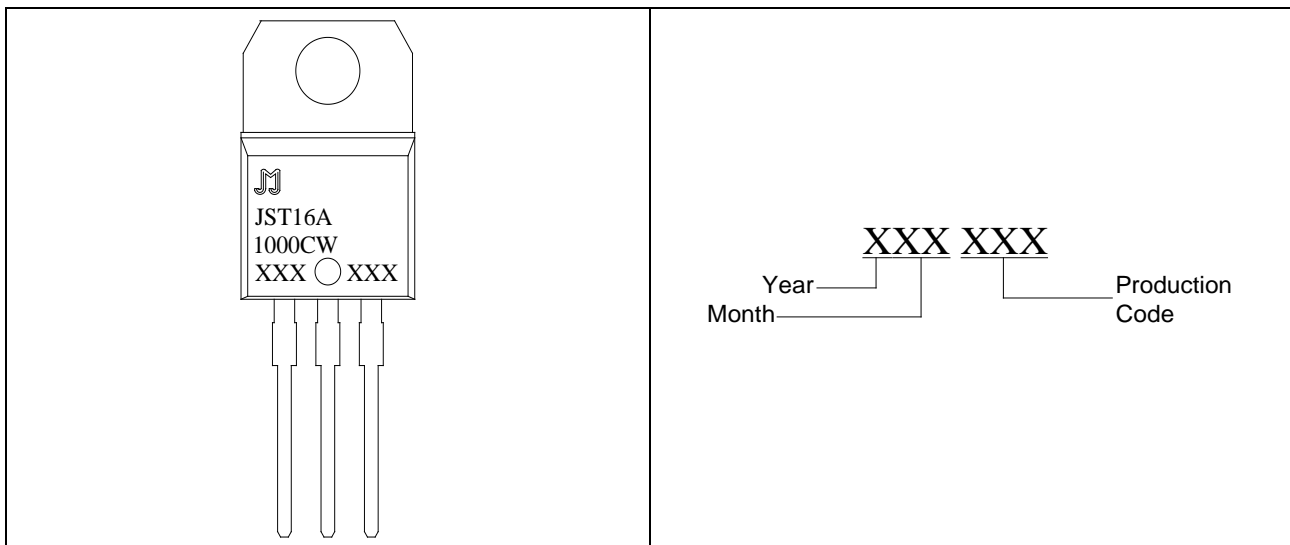
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING



**FIG.1:** Maximum power dissipation versus RMS on-state current

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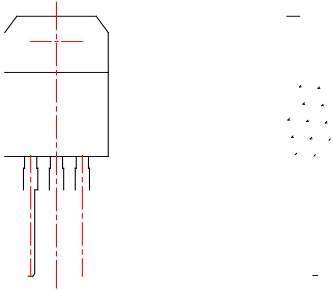
**FIG.2:** RMS on-state current versus case temperature

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards





PACKAGE MECHANICAL DATA



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